

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE3420X uses advanced trench technology to provide excellent $R_{\rm DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a uni-directional or bi-directional load switch.

General Features

• V_{DS} = 20V,I_D = 6A

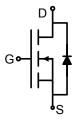
 $R_{DS(ON)} < 45 \text{m}\Omega$ @ $V_{GS} = 2.5 \text{V}$

 $R_{DS(ON)}$ < 33m Ω @ V_{GS} =4.5V

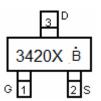
- High Power and current handing capability
- Surface Mount Package
- Pb free terminal plating
- RoHS compliant
- Halogen free

Application

- Uni-directional Load switch
- Bi-directional Load switch



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3420X B	NCE3420X	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _G S	±12	V
Drain Current-Continuous	I _D	6	Α
Drain Current-Pulsed (Note 1)	I _{DM}	24	Α
Maximum Power Dissipation	P _D	1.25	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	$^{\circ}$ C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	100	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	20		-	٧
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1	μA



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NCE3420X

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	•		•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.5	0.8	1.2	V
Drain Course On Ctata Desistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =4.0 A	-	26	45	mΩ
Drain-Source On-State Resistance		V _{GS} =4.5V, I _D =5.0A	-	18.5	33	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =5A	-	25	-	S
Dynamic Characteristics (Note4)	•		•			
Input Capacitance	C _{lss}	V _{DS} =10V,V _{GS} =0V,	-	655	-	PF
Output Capacitance	Coss		-	89	-	PF
Reverse Transfer Capacitance	C _{rss}	- F=1.0MHz	-	88	-	PF
Switching Characteristics (Note 4)				•		
Turn-on Delay Time	t _{d(on)}		-	3	-	nS
Turn-on Rise Time	t _r	V_{DD} =10V, R_L =2 Ω	-	7.5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =3 Ω	-	20	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Qg		-	20	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =10V,I _D =5A,V _{GS} =10V	-	1.3	-	nC
Gate-Drain Charge	Q_{gd}]	-	2.9	-	nC
Drain-Source Diode Characteristics	•		•			-
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =5A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	6	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- $\textbf{2. Surface Mounted on FR4 Board}, \ t \leq 10 \ \text{sec. The } \ R_{\text{0JA}} \ \text{is the sum of the thermal impedence from junction to lead } \ R_{\text{0JL}} \ \text{and lead to ambient}.$
- 3. Pulse Test: Pulse Width ≤ $300\mu s$, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

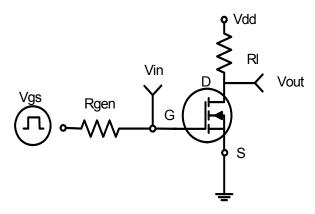


Figure 1:Switching Test Circuit

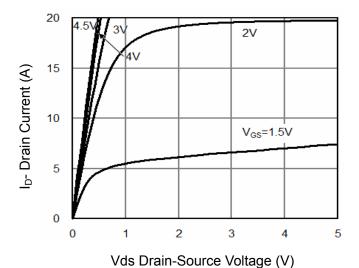


Figure 3 Output Characteristics

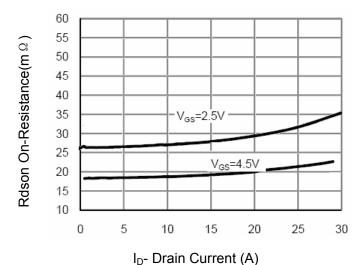


Figure 5 Drain-Source On-Resistance

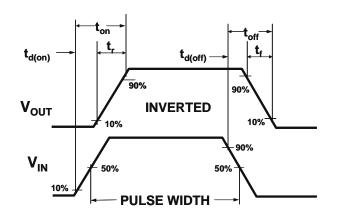


Figure 2:Switching Waveforms

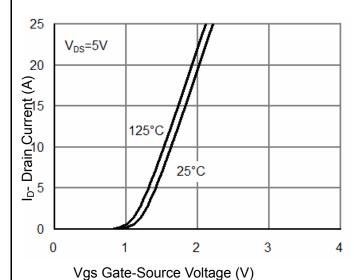


Figure 4 Transfer Characteristics

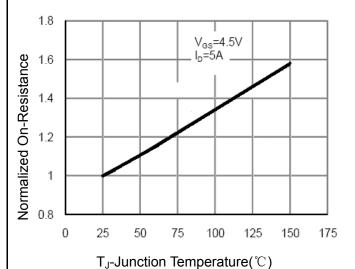
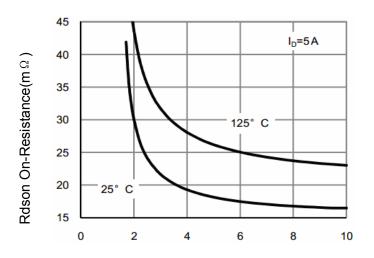
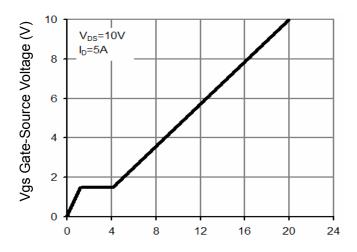


Figure 6 Drain-Source On-Resistance

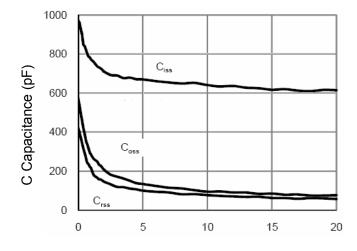




Vgs Gate-Source Voltage (V)
Figure7 Rdson vs Vgs



Qg Gate Charge (nC) Figure 9 Gate Charge



Vds Drain-Source Voltage (V)

Figure 11 Capacitance vs Vds

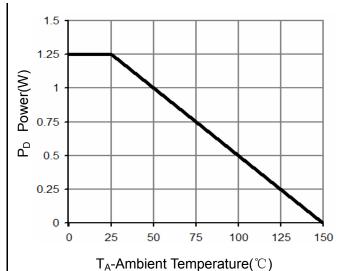


Figure 8 Power Dissipation

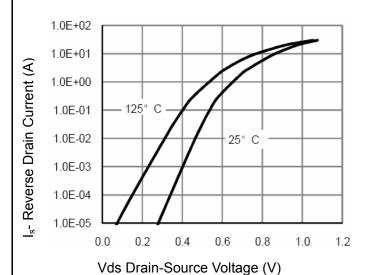
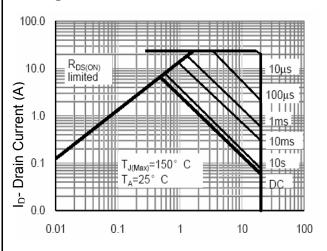


Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area



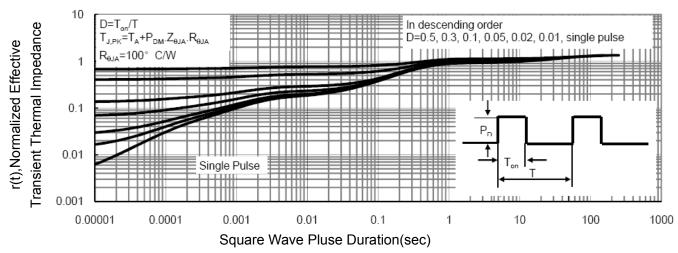
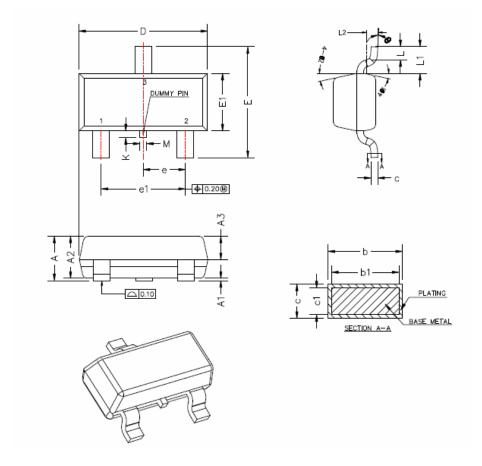


Figure 13 Normalized Maximum Transient Thermal Impedance



SOT-23(E) Package Information



Symbol	Millimeters			
Symbol	Min.	Max.		
Α	0.89	1.12		
A1	0.01	0.10		
A2	0.88	1.02		
A3	0.43	0.63		
b	0.36	0.50		
b1	0.35	0.45		
С	0.14	0.20		
c1	0.14	0.16		
D	2.80	3.00		
E	2.35	2.64		
E1	1.20	1.40		
е	0.90	1.00		
e1	1.80	2.00		
L	0.40	0.60		
L1	0.6REF			
L2	0.25BSC			
θ	0°	8°		
θ1	10°	14°		
θ2	10°	14°		



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